

Customer No.: 31561
Application No.: 10/605,403
Docket No.: 11401-US-PA

In The Claims:

Claim 1. (currently amended) A method for fabricating a thin film transistor (TFT), comprising:

forming a gate on a substrate, the gate comprising a MoNb-alloy composite layer of MoNb/AlNd or MoNb/AlNd/MoNb;

forming an insulating layer over the substrate covering the gate;

forming a channel layer on the insulating layer above the gate; and

forming a source/drain on the channel layer.

Claim 2. (original) The method of claim 1, wherein an amount of niobium in the MoNb alloy is less than 10%.

Claims 3-4. (canceled)

Claim 5. (original) The method of claim 1, wherein the source/drain comprises a single MoNb layer or a composite layer of MoNb/AlNd or MoNb/AlNd/MoNb.

Claim 6. (original) The method of claim 5, wherein an amount of niobium in the MoNb alloy is less than 10%.

Claim 7. (currently amended) A method for fabricating a thin film transistor (TFT), comprising:

forming a gate on a substrate;

forming an insulating layer over the substrate covering the gate;

forming a channel layer on the insulating layer above the gate; and

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forming a source/drain on the channel layer, the source/drain comprising a MoNb alloy composite layer of MoNb/AlNd or MoNb/AlNd/MoNb.

Claim 8. (original) The method of claim 7, wherein an amount of niobium in the MoNb alloy is less than 10%.

Claims 9-10. (canceled)

Claim 11. (currently amended) A thin film transistor (TFT), comprising:
a gate on a substrate, the gate comprising a MoNb alloy composite layer of MoNb/AlNd or MoNb/AlNd/MoNb;

an insulating layer over the substrate covering the gate;
a channel layer on the insulating layer above the gate; and
a source/drain on the channel layer.

Claim 12. (original) The TFT of claim 11, wherein an amount of niobium in the MoNb alloy is less than 10%.

Claims 13-14. (canceled)

Claim 15. (original) The TFT of claim 11, wherein the source/drain comprises a single MoNb layer or a composite layer of MoNb/AlNd or MoNb/AlNd/MoNb.

Claim 16. (original) The TFT of claim 15, wherein an amount of niobium in the MoNb alloy is less than 10%.

Claim 17. (previously presented) A thin film transistor (TFT), comprising:
a gate on a substrate;

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an insulating layer over the substrate covering the gate;
a channel layer on the insulating layer above the gate; and
a source/drain on the channel layer, the source/drain comprising a composite layer
of MoNb/AlNd or MoNb/AlNd/MoNb.

Claim 18. (original) The method of claim 17, wherein an amount of niobium in the
MoNb alloy is less than 10%.

Claims 19-20 (canceled)

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